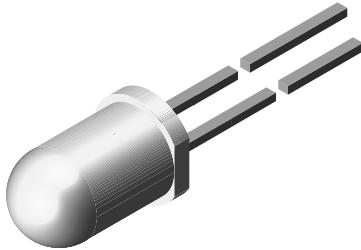


## Infrared Emitting Diode, 875 nm, GaAlAs



94 8389

### DESCRIPTION

The TSHA6500 is an infrared, 875 nm emitting diode in GaAlAs technology, molded in a clear, untinted plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Peak wavelength:  $\lambda_p = 875$  nm
- High reliability
- Angle of half intensity:  $\varphi = \pm 24^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Infrared remote control and free air data transmission systems with comfortable radiation angle
- This emitter is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorption of 875 nm radiation in glass

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSHA6500	30	$\pm 24$	875	600

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHA6500	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu s$	$I_{FSM}$	2.5	A
Power dissipation		$P_V$	180	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 85	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	230	K/W

#### Note

$T_{amb} = 25 \text{ }^\circ C$ , unless otherwise specified

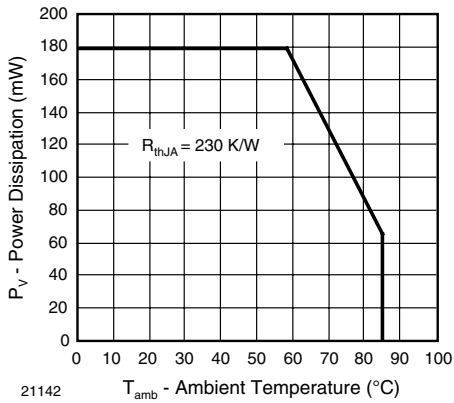


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

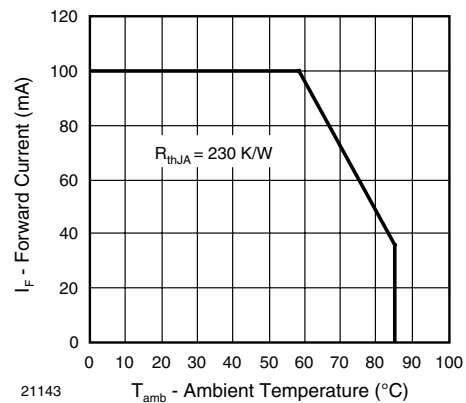
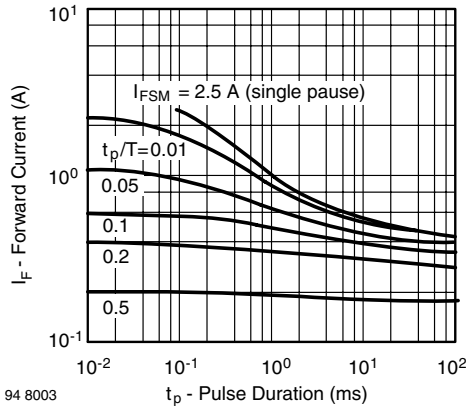


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>		1.5	1.8	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.8	3.5	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>V<sub>F</sub></sub>		- 1.6		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			100	μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>		20		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	I <sub>e</sub>	16	30	48	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	I <sub>e</sub>	128	240		mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	φ <sub>e</sub>		24		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 20 mA	TKφ <sub>e</sub>		- 0.7		%/K
Angle of half intensity		φ		± 24		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>		875		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		80		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		600		ns
	I <sub>F</sub> = 1 A	t <sub>r</sub>		300		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		600		ns
	I <sub>F</sub> = 1 A	t <sub>f</sub>		300		ns
Virtual source diameter		d		2.2		mm

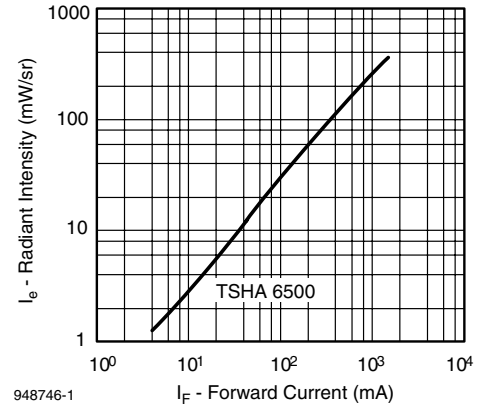
**Note**

T<sub>amb</sub> = 25 °C, unless otherwise specified

**BASIC CHARACTERISTICS**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified


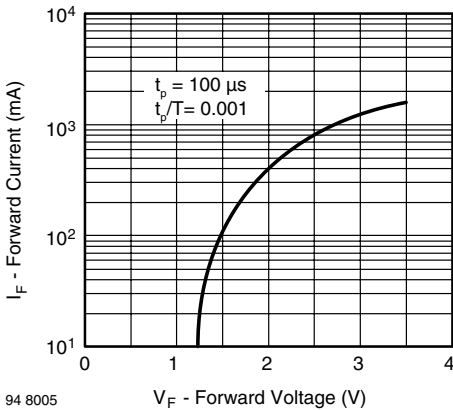
94 8003

Fig. 3 - Pulse Forward Current vs. Pulse Duration



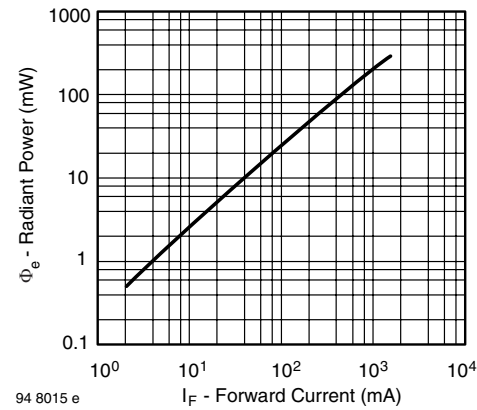
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Fig. 6 - Radiant Intensity vs. Forward Current



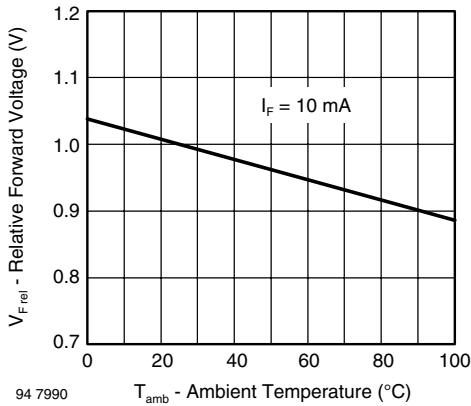
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Fig. 4 - Forward Current vs. Forward Voltage



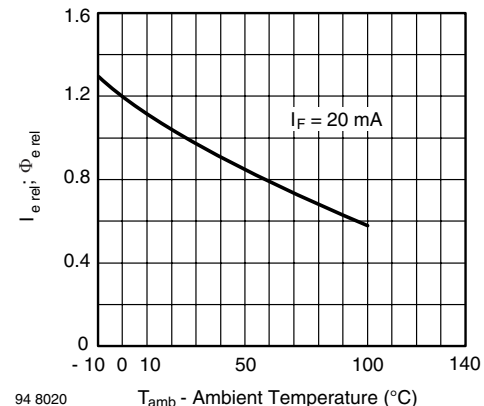
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Fig. 7 - Radiant Power vs. Forward Current



94 7990

Fig. 5 - Relative Forward Voltage vs. Ambient Temperature



94 8020

Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

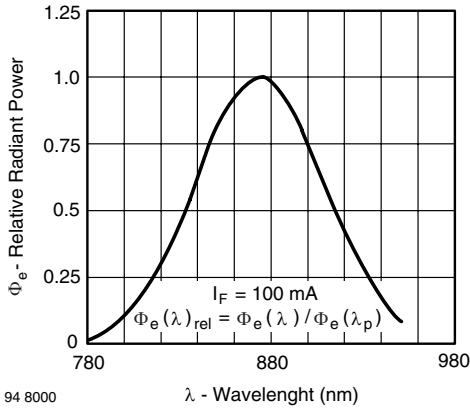


Fig. 9 - Relative Radiant Power vs. Wavelength

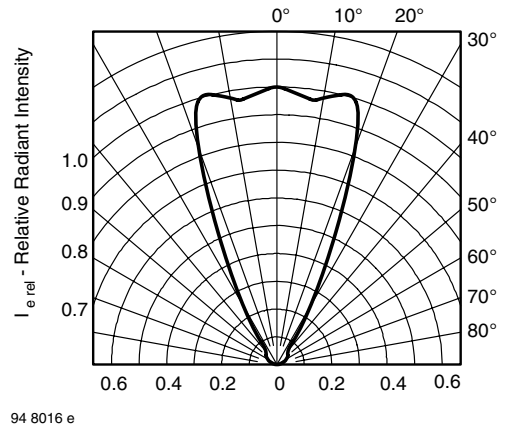
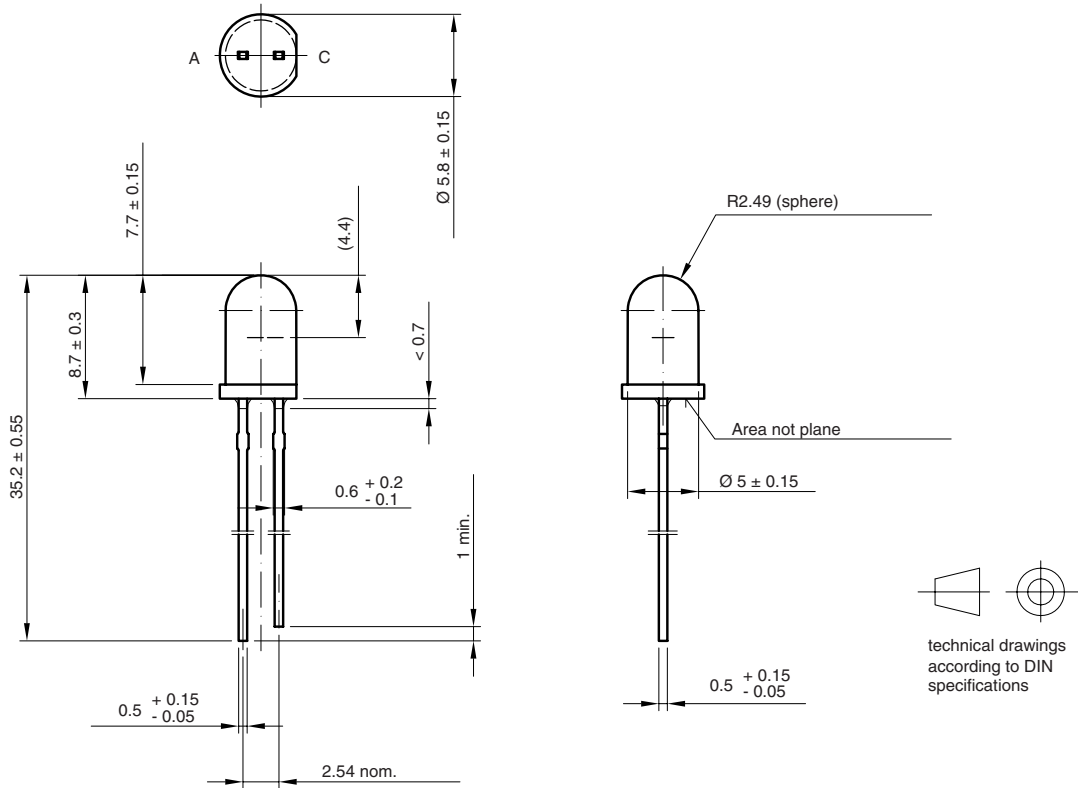


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters



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Issue: 3; 19.05.09  
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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

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